RoHS

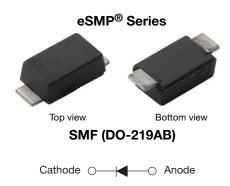
COMPLIANT HALOGEN

FREE

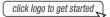


### Vishay Semiconductors

# Ultrafast Rectifier, 2 A FRED Pt®



#### **DESIGN SUPPORT TOOLS**

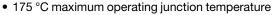




PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	2 A			
$V_{R}$	600 V			
V <sub>F</sub> at I <sub>F</sub>	0.95 V			
t <sub>rr</sub>	55 ns			
T <sub>J</sub> max.	175 °C			
Package	SMF (DO-219AB)			
Circuit configuration	Single			

#### **FEATURES**

 $\bullet$  Ultrafast recovery time, reduced  $\mathbf{Q}_{\text{rr}},$  and soft recovery



- For PCF CRM, snubber operation
- · Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Wave and reflow solderable
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **DESCRIPTION / APPLICATIONS**

State of the art ultrafast recovery rectifiers designed with optimized performance of forward voltage drop, ultrafast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in PFC, boost, lighting, in the AC/DC section of SMPS, freewheeling and clamp diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	$V_{RRM}$		600	V
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 135 °C <sup>(1)</sup>	2	۸
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C, 6 ms square pulse	30	А
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C

#### Note

<sup>(1)</sup> Device on PCB with 8 mm x 16 mm soldering lands

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	Ι <sub>R</sub> = 100 μΑ	600	-	-	
Formulated voltage	I <sub>F</sub> = 2 A	-	1.10	1.35	V	
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 2 A, T <sub>J</sub> = 150 °C	-	0.95	1.15	
Deverage leakers as wrent		$V_R = V_R$ rated	-	-	3	
Reverse leakage current I <sub>R</sub>	I <sub>R</sub>	T <sub>J</sub> = 150 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	20	100	μΑ
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 600 V	-	5	-	pF



<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 A, dI_F/dt = 50 A$	/μs, V <sub>R</sub> = 30 V	-	42	-	
Reverse recovery time	t <sub>rr</sub>	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	-	55	
neverse recovery time		T <sub>J</sub> = 25 °C		-	40	-	ns
		T <sub>J</sub> = 125 °C		-	63	-	
Dools weeks as weeks		T <sub>J</sub> = 25 °C	I <sub>F</sub> = 2 A	-	7.0	-	Α
Peak recovery current I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	dI <sub>F</sub> /dt = 500 A/µs V <sub>R</sub> = 400 V	-	8.1	-		
Reverse recovery charge Q <sub>rr</sub>	0	T <sub>J</sub> = 25 °C		-	140	-	nC
	T <sub>J</sub> = 125 °C		-	255	-	iiC	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	+175	°C
Thermal resistance, junction to case	R <sub>thJC</sub>	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	-	15	°C/W
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Device mounted on PCB with 2 mm x 3.5 mm soldering lands	-	-	130	°C/W
Approximate weight				0.015		g
Approximate weight				0.0005		OZ.
Marking device		Case style SMF (DO-219AB)		М	PU	

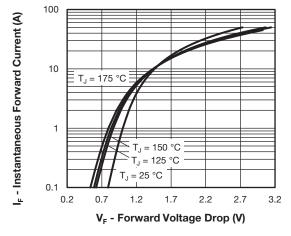


Fig. 1 - Typical Forward Voltage Drop Characteristics

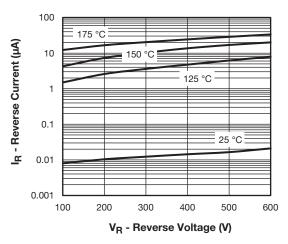


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

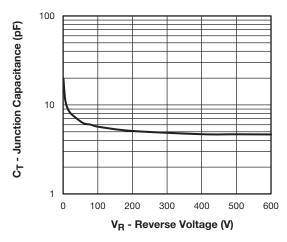


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

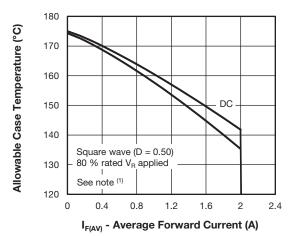
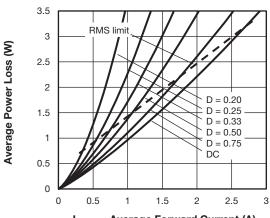


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current



I<sub>F(AV)</sub> - Average Forward Current (A) Fig. 5 - Forward Power Loss Characteristics



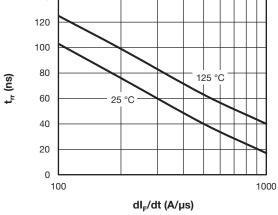


Fig. 6 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

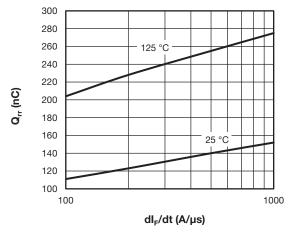
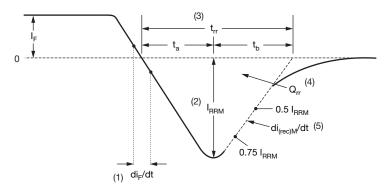


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ; Pd = forward power loss =  $I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig. 5);  $Pd_{REV}$  = inverse power loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1}$  = rated  $V_R$ 

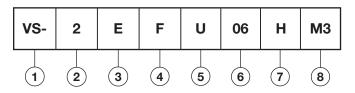


- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (4)  $Q_{rr}$  area under curve defined by  $t_{rr}$  and  $I_{RRM}$
- (2) I<sub>RRM</sub> peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3)  $t_{\rm rr}$  reverse recovery time measured from zero crossing point of negative going  $I_{\rm F}$  to point where a line passing through 0.75  $I_{\rm RRM}$  and 0.50  $I_{\rm RRM}$  extrapolated to zero current.
- (5)  $di_{(rec)M}/dt$  peak rate of change of current during  $t_b$  portion of  $t_{rr}$

Fig. 8 - Reverse Recovery Waveform and Definitions

#### **ORDERING INFORMATION TABLE**

#### **Device code**



- Vishay Semiconductors product
- Current rating (2 = 2 A)
- 3 Circuit configuration:

E = single diode

4 - F = SMF package

5 - Process type,

U = ultrafast recovery

6 - Voltage code (06 = 600 V)

7 - H = AEC-Q101 qualified

8 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

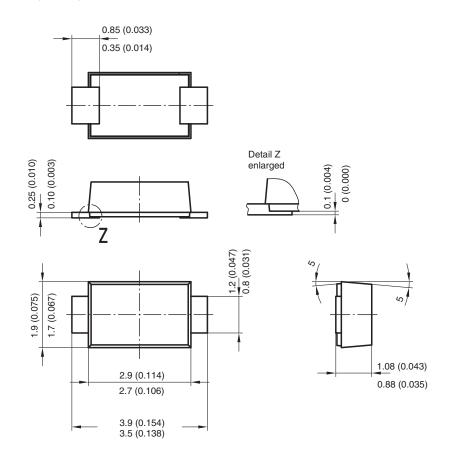
ORDERING INFORMATION (Example)					
PREFERRED P/N QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION					
VS-2EFU06HM3/I	10 000	10 000	13" diameter plastic tape and reel		

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95572			
Part marking information	www.vishay.com/doc?95618			
Packaging information	www.vishay.com/doc?95577			

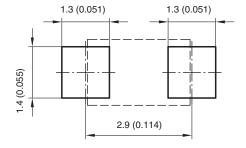


# **SMF (DO-219AB)**

### **DIMENSIONS** in millimeters (inches)



#### Foot print recommendation:



Created - Date: 15. February 2005 Rev. 3 - Date: 13. March 2007 Document no.:S8-V-3915.01-001 (4) 17247



### **Legal Disclaimer Notice**

Vishay

### **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

## **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Rectifiers category:

Click to view products by Vishay manufacturer:

Other Similar products are found below:

D91A DA24F4100L DD89N1600K-A DD89N16K-K RL252-TP DSEI2X30-06C 1N4005-TR BAV199-TP UFS120Je3/TR13

JANS1N6640US DD89N16K DD89N16K-A 481235F 067907F MS306 ND104N08K SPA2003-B-D-A01 US2JFL-TP UFS105Je3/TR13

A1N5404G-G ACGRA4007-HF ACGRB207-HF RF301B2STL RF501B2STL UES1302 BAV199E6433HTMA1 ACGRC307-HF

ACEFC304-HF JANTXV1N5660A UES1106 GS2K-LTP D126A45C D251N08B SCHJ22.5K SM100 SCPA2 SDHD5K STTH20P035FP

VS-8EWS12S-M3 VS-12FL100S10 ACGRA4001-HF MUR420GP-TP 1N5404GP-E3/54 ND89N08K D1821SH45T PR D1251S45T

JANTX1N3890 SKN20/16 SKN70/16 1N3660R